



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

NTE2691 (NPN) & NTE2692 (PNP) Silicon Complementary Transistors High Voltage Switch

Features:

- High Breakdown Voltage
- Large Current Capacity

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

| | |
|--|-------------------------------------|
| Collector–Base Voltage, V_{CBO} | 180V |
| Collector–Emitter Voltage, V_{CEO} | 160V |
| Emitter–Base Voltage, V_{EBO} | 6V |
| Collector Current, I_C | |
| Continuous | 1.5A |
| Pulse | 2.5A |
| Collector Dissipation, P_C | 1W |
| Maximum Junction Temperature, T_J | $+150^\circ\text{C}$ |
| Storage Temperature Range, T_{stg} | -55° to $+150^\circ\text{C}$ |

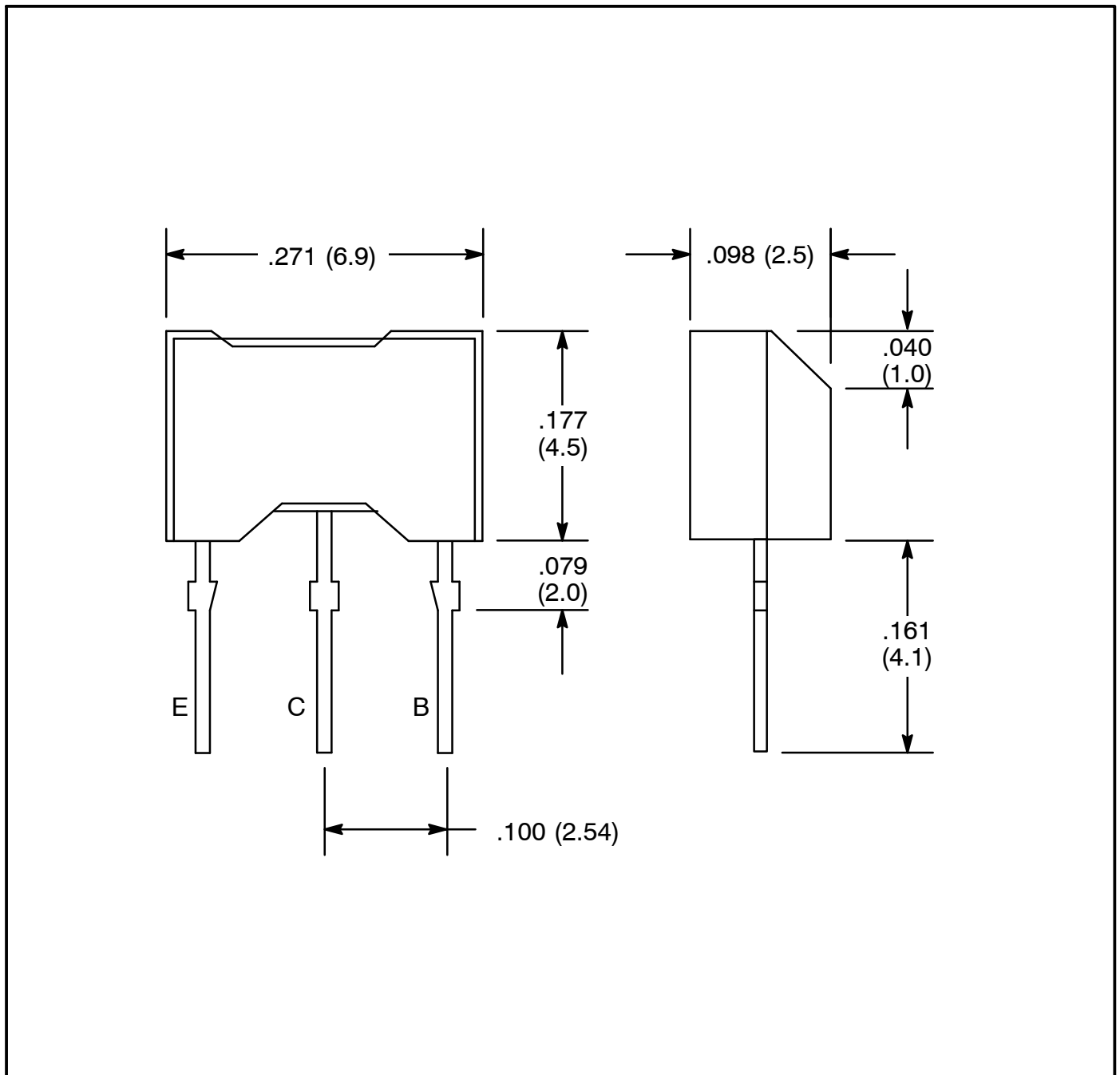
Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---------------|--|-----|------|-----|---------------|
| Collector Cutoff Current | I_{CBO} | $V_{CB} = 120\text{V}, I_E = 0$ | – | – | 1 | μA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB} = 4\text{V}, I_C = 0$ | – | – | 1 | μA |
| DC Current Gain NTE2691 | h_{FE1} | $V_{CE} = 5\text{V}, I_C = 100\text{mA}$ | 140 | – | 280 | |
| NTE2692 | | | 200 | – | 400 | |
| DC Current Gain | h_{FE2} | $V_{CE} = 5\text{V}, I_C = 10\text{mA}$ | 80 | – | – | |
| Gain–Bandwidth Product | f_T | $V_{CE} = 10\text{V}, I_C = 50\text{mA}$ | – | 120 | – | MHz |
| Output Capacitance NTE2691 | C_{ob} | $V_{CB} = 10\text{V}, f = 1\text{MHz}$ | – | 14 | – | pF |
| NTE2692 | | | – | 22 | – | pF |
| Collector–Emitter Saturation Voltage NTE2691 | $V_{CE(sat)}$ | $I_C = 500\text{mA}, I_B = 50\text{mA}$ | – | 130 | 450 | mV |
| NTE2692 | | | – | 200 | 500 | mV |
| Base–Emitter Saturation Voltage | $V_{BE(sat)}$ | $I_C = 500\text{mA}, I_B = 50\text{mA}$ | – | 0.85 | 1.2 | V |



Electrical Characteristics (Cont'd): ($T_A = +25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|-------------------------------------|---------------|---|-----|-----|-----|---------------|
| Collector-Base Breakdown Voltage | $V_{(BR)CBO}$ | $I_C = 10\mu\text{A}, I_E = 0$ | 180 | - | - | V |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | $I_C = 1\text{mA}, R_{BE} = \infty$ | 160 | - | - | V |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | $I_E = 10\mu\text{A}, I_C = 0$ | 6 | - | - | V |
| Turn-On Time | t_{on} | $I_C = 10\text{I}_{B1} = -10\text{I}_{B1} = 700\text{mA},$ $V_{CC} = 100\text{V}, \text{Pulse Width} = 20\mu\text{s},$ $\text{Duty Cycle} \leq 1\%$ | - | 40 | - | μs |
| Storage Time NTE2691 | t_{stg} | | - | 1.2 | - | μs |
| NTE2692 | | | - | 0.7 | - | μs |
| Fall Time NTE2691 | t_f | | - | 80 | - | ns |
| NTE2692 | | - | 40 | - | ns | |



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [NTE manufacturer](#):

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MJ15024/WS](#) [MJ15025/WS](#) [BC546/116](#) [BC556/FSC](#) [BC557/116](#) [BSW67A](#) [HN7G01FU-A\(T5L,F,T](#)
[NJVMJD148T4G](#) [NSVMMBT6520LT1G](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE2353](#) [NTE316](#) [IMX9T110](#) [NTE63](#) [NTE65](#)
[C4460](#) [SBC846BLT3G](#) [2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA1727TLP](#) [2SA2126-E](#) [2SB1202T-TL-E](#) [2SB1204S-TL-E](#) [2SC5488A-](#)
[TL-H](#) [2SD2150T100R](#) [SP000011176](#) [FMC5AT148](#) [2N2369ADCSM](#) [2SB1202S-TL-E](#) [2SC2412KT146S](#) [2SC4618TLN](#) [2SC5490A-TL-H](#)
[2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [BC557B](#) [TTC012\(Q\)](#) [BULD128DT4](#) [JANTX2N3810](#)
[Jantx2N5416](#) [US6T6TR](#) [KSF350](#) [068071B](#)